

Replaces July 1999 version, DS4334-4.0

DG858DW45

Gate Turn-Off Thyristor

DS4334-4.1 M	ay 2000
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FEATURES

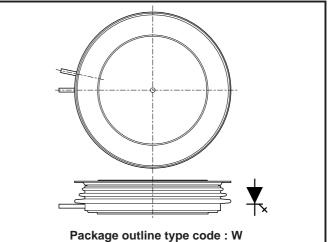
- Double Side Cooling
- High Reliability In Service
- High Voltage Capability
- Fault Protection Without Fuses
- High Surge Current Capability
- Turn-off Capability Allows Reduction In Equipment Size And Weight. Low Noise Emission Reduces Acoustic Cladding Necessary For Environmental Requirements

APPLICATIONS

- Variable speed A.C. motor drive inverters (VSD-AC).
- Uninterruptable Power Supplies
- High Voltage Converters.
- Choppers.
- Welding.
- Induction Heating.
- DC/DC Converters.

VOLTAGE RATINGS

KEY PAR	AMETERS
I _{TCM}	3000A
V	4500V
	1100A
I _{⊤(AV)} dV _□ /dt	750V/ μs
dl _T /dt	300Α/μs



Package outline type code : W See Package Details for further information.

Fig.1 Package outline

Type Number	Repetitive Peak Off-state Voltage V _{DRM} V	Repetitive Peak Reverse Voltage V _{RRM} V	Conditions
DG858DW45	4500	16	$T_{vj} = 125^{\circ}C, I_{DRM} = 100mA,$ $I_{RRM} = 50mA$

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TCM}	Repetitive peak controllable on-state current	$ \begin{array}{l} V_{_{D}}=V_{_{DRM}},T_{_{j}}=125^{\circ}C,di_{_{GQ}}/dt=40A/\mus,\\ Cs=4.0\muF,L_{_{S}}\leq200nH \end{array} $	3000	A
I _{T(AV)}	Mean on-state current	$T_{HS} = 80^{\circ}C$. Double side cooled, half sine 50Hz.	1100	А
I _{T(RMS)}	RMS on-state current	$T_{HS} = 80^{\circ}C$. Double side cooled, half sine 50Hz.	1720	А

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine. T _j = 125°C	20.0	kA
l²t	I ² t for fusing	10ms half sine. T _j =125°C	2.0 x 10 ⁶	A ² s
di _r /dt	Critical rate of rise of on-state current	V _D = 3000V, I _T = 3000A, T _j =125°C I _{FG} > 40A, Rise time < 1.0μs	300	A/μs
D. (.).		To 66% V_{DRM} ; $R_{GK} \le 22\Omega$, $T_j = 125^{\circ}C$	20	V/µs
dV _D /dt	Rate of rise of off-state voltage	To 66% V _{DRM} ; V _{RG} = -2V, T _j = 125°C	750	V/µs
L _s	Peak stray inductance in snubber circuit	$I_{T} = 3000A, V_{D} = V_{DRM}, T_{j} = 125^{\circ}C,$ $di_{GQ}/dt = 40A/\mu s, Cs = 4.0\mu F$	200	nH

GATE RATINGS

Symbol	Parameter	Conditions	Min.	Max.	Units
V _{RGM}	Peak reverse gate voltage	This value maybe exceeded during turn-off	-	16	V
I _{FGM}	Peak forward gate current		20	100	А
P _{FG(AV)}	Average forward gate power		-	20	W
P _{RGM}	Peak reverse gate power		-	24	kW
di _{gq} /dt	Rate of rise of reverse gate current		20	60	A/μs
t _{on(min)}	Minimum permissable on time		50	-	μs
t _{OFF(min)}	Minimum permissable off time		100	-	μs

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
		Double side cooled		-	0.011	°C/W
R _{th(j-hs)}	DC thermal resistance - junction to	Anode side cooled		-	0.017	°C/W
	heatsink surface	Cathode side cooled		-	0.03	°C/W
R _{th(c-hs)}	Contact thermal resistance	Clamping force 40kN With mounting compound	per contact	-	0.0021	°C/W
T _{vj}	Virtual junction temperature			-40	125	°C
T _{OP} /T _{stg}	Operating junction/storage temperature range			-40	125	°C
-	Clamping force			36.0	44.0	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Max.	Units
V _{TM}	On-state voltage	At 3000A peak, I _{G(ON)} = 10A d.c.	-	3.85	V
I _{DM}	Peak off-state current	V _{DRM} = 4500V, V _{RG} = 2V	-	100	mA
I _{RRM}	Peak reverse current	At V _{RRM}	-	50	mA
V _{gt}	Gate trigger voltage	$V_{\rm D} = 24V, I_{\rm T} = 100A, T_{\rm j} = 25^{\circ}{\rm C}$	-	1.2	V
I _{GT}	Gate trigger current	$V_{\rm D} = 24V, I_{\rm T} = 100A, T_{\rm j} = 25^{\circ}{\rm C}$	-	4.0	A
I _{RGM}	Reverse gate cathode current	V _{RGM} = 16V, No gate/cathode resistor	-	50	mA
E _{ON}	Turn-on energy	V _D = 2000V	-	4400	mJ
t _d	Delay time	I _τ = 3000A, dI _τ /dt = 300A/μs	-	2.0	μs
t _r	Rise time	$I_{FG} = 40A$, rise time < 1.0µs	-	6.0	μs
E_{OFF}	Turn-off energy		-	12500	mJ
t _{gs}	Storage time		-	26	μs
t _{gf}	Fall time	I _T = 3000A, V _{DM} = 4200V	-	2.5	μs
t _{gq}	Gate controlled turn-off time	Snubber Cap Cs = 4.0μF,	-	28.5	μs
Q _{GQ}	Turn-off gate charge	$di_{GQ}/dt = 40/\mu s$	-	12500	μC
$Q_{_{\mathrm{GQT}}}$	Total turn-off gate charge		-	25000	μC
I _{GQM}	Peak reverse gate current		-	950	Α

RELIABILITY

	Conditions	Limit	Units
DC blocking reliability	V_{dc} = 3500V, T_j = -40 to + 125°C, ambient cosmic radiation at sea level, in open air, 100% duty cycle.	100	FIT

CURVES

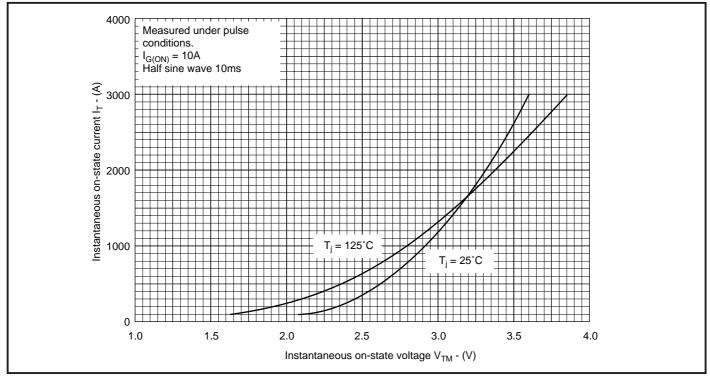


Figure 2. On-state characteristics

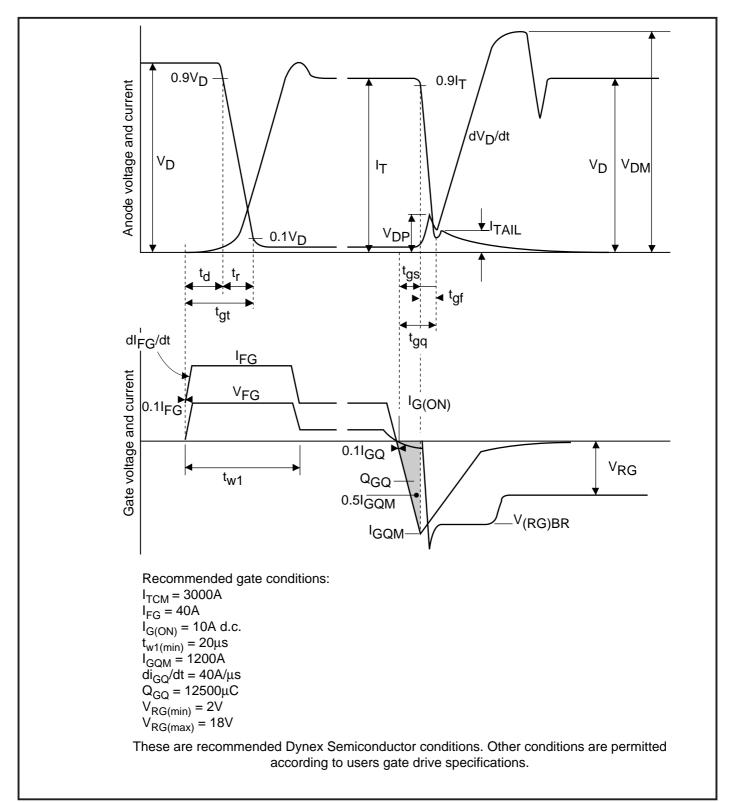
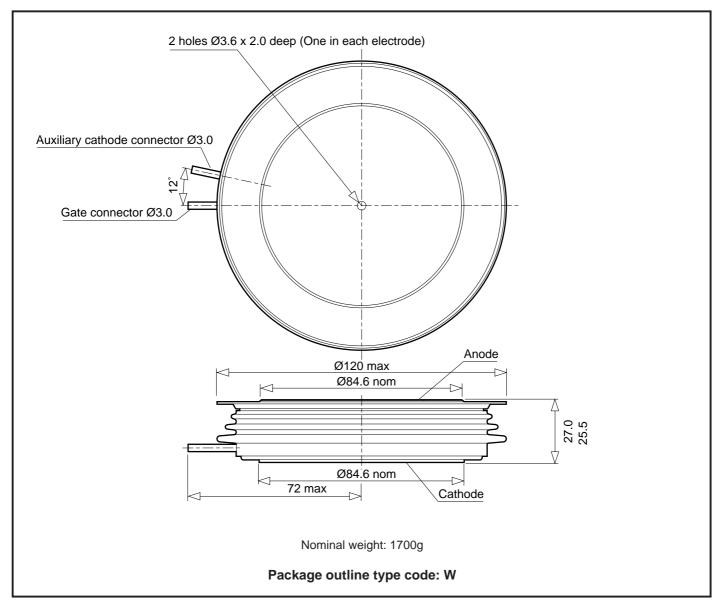


Figure 3. General switching waveforms

PACKAGE DETAILS

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Associated Literature/Products Publication No. Title/Part Number

AN4571	Application note - GDU9X-XXXXX Series GTO gate drive units.
DS4567	GDU90-20721 GTO gate drive unit.
DS4568	GDU90-20722 GTO gate drive unit.
DS4150	DSF8045SK - Snubber diode.
DS4153	DSF21545SV - Antiparallel/freewheel diode.

6/7



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